

Abstract

To provide an impurity introducing method which can repeatedly carry out such a process that plasma irradiation for realization of amorphous and plasma doping were combined, in
5 such a situation that steps are simple and through-put is high, without destroying an apparatus.

At the time of switching over plasmas which are used in plasma irradiation for realization of amorphous and plasma doping, electric discharge is stopped, and an initial condition of a
10 matching point of a high frequency power supply and a peripheral circuit is reset so as to adapt to plasma which is used in each step, or at the time of switching, a load, which is applied to the high frequency power supply etc., is reduced by increasing pressure and decreasing a bias voltage.

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